Table of Contents

Preface xiii

Chapter 1. Adsorption Phenomena 1

1.1. The surface of solids: general points 1
1.2. Illustration of adsorption 2
  1.2.1. The volumetric method or manometry 3
  1.2.2. The gravimetric method or thermogravimetry 4
1.3. Acting forces between a gas molecule and the surface of a solid 4
  1.3.1. Van der Waals forces 4
  1.3.2. Expression of the potential between a molecule and a solid 6
  1.3.3. Chemical forces between a gas species and the surface of a solid . . 7
  1.3.4. Distinction between physical and chemical adsorption 8
1.4. Thermodynamic study of physical adsorption 8
  1.4.1. The different models of adsorption 8
  1.4.2. The Hill model 9
  1.4.3. The Hill-Everett model 10
  1.4.4. Thermodynamics of the adsorption equilibrium in Hill's model . . . 10
    1.4.4.1. Formulating the equilibrium 10
    1.4.4.2. Isotherm equation 11
  1.4.5. Thermodynamics of adsorption equilibrium in the Hill-Everett model 12
1.5. Physical adsorption isotherms 13
  1.5.1. General points 13
  1.5.2. Adsorption isotherms of mobile monolayers 15
  1.5.3. Adsorption isotherms of localized monolayers 15
    1.5.3.1. Thermodynamic method 16
    1.5.3.2. The kinetic model 17
  1.5.4. Multilayer adsorption isotherms 18
    1.5.4.1. Isotherm equation 18

1.6. Chemical adsorption isotherms 23
1.7. Bibliography 27

Chapter 2. Structure of Solids: Physico-chemical Aspects 29

2.1. The concept of phases 29
2.2. Solid solutions 31
2.3. Point defects in solids 33
2.4. Denotation of structural members of a crystal lattice. 34
2.5. Formation of structural point defects 36
  2.5.1. Formation of defects in a solid matrix 36
  2.5.2. Formation of defects involving surface elements 37
  2.5.3. Concept of elementary hopping step 38
2.6. Bibliography 38

Chapter 3. Gas-Solid Interactions: Electronic Aspects 39

3.1. Introduction 39
3.2. Electronic properties of gases 39
3.3. Electronic properties of solids 40
  3.3.1. Introduction 40
  3.3.2. Energy spectrum of a crystal lattice electron. 41
    3.3.2.1. Reminder about quantum mechanics principles 41
    3.3.2.2. Band diagrams of solids. 45
    3.3.2.3. Effective mass of an electron 52
3.4. Electrical conductivity in solids 55
  3.4.1. Full bands 55
  3.4.2. Partially occupied bands 56
3.5. Influence of temperature on the electric behavior of solids 57
  3.5.1. Band diagram and Fermi level of conductors 57
  3.5.2. Case of intrinsic semiconductors 61
  3.5.3. Case of extrinsic semiconductors 62
  3.5.4. Case of materials with point defects. 64
    3.5.4.1. Metal oxides with anion defects, denoted by MO_{1-x} 65
    3.5.4.2. Metal oxides with cation vacancies, denoted by $M_{1-x}O$ 66
    3.5.4.3. Metal oxides with interstitial cations, denoted by $M_{1+x}O$ 67
    3.5.4.4. Metal oxides with interstitial anions, denoted by MO_{1+x}. 67
3.6. Bibliography 68

Chapter 4. Interfacial Thermodynamic Equilibrium Studies 69

4.1. Introduction 69
4.2. Interfacial phenomena 70
4.3. Solid-gas equilibriums involving electron transfers or electron holes . . . 71
  4.3.1. Concept of surface states 72

4.3.2. Space-charge region (SCR) . . . 73
4.3.3. Electronic work function . . . 77
4.3.3.1. Case of a semiconductor in the absence of surface states . . . 77
4.3.3.2. Case of a semiconductor in the presence of surface states . . . 78
4.3.3.3. Physicists' and electrochemists' denotation systems . . . 79
4.3.4. Influence of adsorption on the electron work functions . . . 80
4.3.4.1. Influence of adsorption on the surface barrier V_S . . . 80
4.3.4.2. Influence of adsorption on the dipole component V_D. . . . 90
4.4. Solid-gas equilibriums involving mass and charge transfers . . . 91
4.4.1. Solids with anion vacancies . . . 92
4.4.2. Solids with interstitial cations . . . 94
4.4.3. Solids with interstitial anions . . . 94
4.4.4. Solids with cation vacancies . . . 96
4.5. Homogenous semiconductor interfaces . . . 97
4.5.1. The electrostatic potential is associated with the intrinsic energy level . . . 103
4.5.2. Electrochemical aspect . . . 104
4.5.3. Polarization of the junction . . . 107
4.6. Heterogenous junction of semiconductor metals . . . 107
4.7. Bibliography . . . 108

Chapter 5. Model Development for Interfacial Phenomena . . . 109

5.1. General points on process kinetics . . . 109
5.1.1. Linear chain . . . 111
5.1.1.1. Pure kinetic case hypothesis . . . 114
5.1.1.2. Bodenstein's stationary state hypothesis . . . 118
5.1.1.3. Evolution of the rate according to time and gas pressure . . . 119
5.1.1.4. Diffusion in a homogenous solid phase . . . 121
5.1.2. Branched processes . . . 125
5.2. Electrochemical aspect of kinetic processes . . . 126
5.3. Expression of mixed potential . . . 133
5.4. Bibliography . . . 136

Chapter 6. Apparatus for Experimental Studies: Examples of Applications . . . 137

6.1. Introduction . . . 137
6.2. Calorimetry . . . 138
6.2.1. General points . . . 138
6.2.1.1. Theoretical aspect of Tian-Calvet calorimeters . . . 139
6.2.1.2. Seebeck effect . . . 139
6.2.1.3. Peltier effect . . . 140
6.2.1.4. Tian equation . . . 140

    - 6.2.1.5. Description of a Tian-Calvet device 142
    - 6.2.1.6. Thermogram profile 144
    - 6.2.1.7. Examples of applications 146
- 6.3. Thermodesorption 156
  - 6.3.1. Introduction 156
  - 6.3.2. Theoretical aspect 157
  - 6.3.3. Display of results 161
    - 6.3.3.1. Tin dioxide 161
    - 6.3.3.2. Nickel oxide 163
- 6.4. Vibrating capacitor methods 172
  - 6.4.1. Contact potential difference 172
  - 6.4.2. Working principle of the vibrating capacitor method 176
    - 6.4.2.1. Introduction 176
    - 6.4.2.2. Theoretical study of the vibrating capacitor method 176
  - 6.4.3. Advantages of using the vibrating capacitor technique 179
    - 6.4.3.1. The materials studied 179
    - 6.4.3.2. Temperature conditions 179
    - 6.4.3.3. Pressure conditions 181
  - 6.4.4. The constraints 181
    - 6.4.4.1. The reference electrode 181
    - 6.4.4.2. Capacitance modulation 182
  - 6.4.5. Display of experimental results 182
    - 6.4.5.1. Study of interactions between oxygen and tin dioxide 184
    - 6.4.5.2. Study of interactions between oxygen and beta-alumina 185
- 6.5. Electrical interface characterization 187
  - 6.5.1. General points 187
  - 6.5.2. Direct-current measurement 189
  - 6.5.3. Alternating-current measurement 191
    - 6.5.3.1. General points 191
    - 6.5.3.2. Principle of the impedance spectroscopy technique 191
  - 6.5.4. Application of impedance spectroscopy – experimental results . . . 196
    - 6.5.4.1. Protocol 196
    - 6.5.4.2. Experimental results: characteristics specific to each material . 197
  - 6.5.5. Evolution of electrical parameters according to temperature 202
  - 6.5.6. Evolution of electrical parameters according to pressure 208
- 6.6. Bibliography 212

Chapter 7. Material Elaboration 215

- 7.1. Introduction 215
- 7.2. Tin dioxide 216
  - 7.2.1. The compression of powders 216
    - 7.2.1.1. Elaboration process and structural properties 216

7.2.1.2. Influence of the morphological parameters on the electric properties . . . 217
7.2.2. Reactive evaporation. . . . 219
7.2.2.1. Experimental device . . . 219
7.2.2.2. Measure of the source temperature . . . 222
7.2.2.3. Thickness measure . . . 222
7.2.2.4. Experimental process . . . 224
7.2.2.5. Structure and properties of the films . . . 224
7.2.3. Chemical vapor deposition: deposit contained between 50 and 300 Å. . . . 236
7.2.3.1. General points. . . . 236
7.2.3.2. Device description . . . 238
7.2.3.3. Structural characterization of the material . . . 242
7.2.3.4. Influence of the experimental parameters on the physico-chemical properties of the films. . . . 245
7.2.3.5. Influence of the structure parameters on the electric properties of the films . . . 250
7.2.4. Elaboration of thick films using serigraphy . . . 252
7.2.4.1. Method description. . . . 252
7.2.4.2. Ink elaboration . . . 253
7.2.4.3. Structural characterization of thick films made with tin dioxide . . . 254
7.3. Beta-alumina . . . 255
7.3.1. General properties . . . 255
7.3.2. Material elaboration . . . 257
7.3.3. Material shaping . . . 261
7.3.3.1. Mono-axial compression . . . 261
7.3.3.2. Serigraphic process. . . . 262
7.3.4. Characterization of materials. . . . 263
7.3.4.1. Physico-chemical characterization of the sintered materials . . 263
7.3.4.2. Physico-chemical treatment of the thick films. . . . 266
7.3.5. Electric characterization. . . . 273
7.4. Bibliography . . . 275

Chapter 8. Influence of the Metallic Components on the Electrical Response of the Sensors . . . 277

8.1. Introduction . . . 277
8.2. General points. . . . 278
8.2.1. Methods to deposit the metallic parts on the sensitive element. . . . 278
8.2.2. Role of the metallic elements on the sensors' response . . . 279
8.2.3. Role of the metal: catalytic aspects . . . 282
8.2.3.1. Spill-over mechanism . . . 283

8.2.3.2. Reverse spill-over mechanism 284
8.2.3.3. Electronic effect mechanism 284
8.2.3.4. Influence of the metal nature on the involved mechanism. . . . 286
8.3. Case study: tin dioxide 288
8.3.1. Choice of the samples 288
8.3.2. Description of the reactor 289
8.3.3. Experimental results 291
8.3.3.1. Influence of the oxygen pressure on the electric conductivity . 291
8.3.3.2. Influence of the reducing gas on the electric conductions 295
8.4. Case study: beta-alumina 296
8.4.1. Device and experimental process 297
8.4.2. Influence of the nature of the electrodes on the measured voltage . . 298
8.4.2.1. Study of the different couples of metallic electrodes 299
8.4.2.2. Electric response to polluting gases 301
8.4.3. Influence of the electrode size 303
8.4.3.1. Description of the studied devices. 303
8.4.3.2. Study of the electric response according to the experimental conditions 304
8.5. Conclusion. 306
8.6. Bibliography 307

Chapter 9. Development and Use of Different Gas Sensors 309

9.1. General points on development and use 309
9.2. Examples of gas sensor development. 310
9.2.1. Sensors elaborated using sintered materials 310
9.2.2. Sensors produced with serigraphed sensitive materials 312
9.3. Device designed for the laboratory assessment of sensitive elements and/or sensors to gas action 316
9.3.1. Measure cell for sensitive materials. 317
9.3.2. Test bench for complete sensors 319
9.3.3. Measure of the signal 319
9.3.3.1. Measure of the electric conductance 319
9.3.3.2. Measure of the potential. 322
9.4. Assessment of performance in the laboratory 322
9.4.1. Assessment of the performances of tin dioxide in the presence of gases 322
9.4.2. Assessment of beta-alumina in the presence of oxygen 327
9.4.2.1. Device and experimental process 327
9.4.2.2. Electric response to the action of oxygen. 327
9.4.3. Assessment of the performances of beta-alumina in the presence of carbon monoxide 329
9.4.3.1. Measurement device 329

9.4.3.2. Electric results 329
9.5. Assessment of the sensor working for an industrial application 332
9.5.1. Detection of hydrogen leaks on a cryogenic engine 333
9.5.1.1. Context of the study 333
9.5.1.2. Study of performances in the presence of hydrogen 333
9.5.1.3. Test carried out in an industrial environment 337
9.5.2. Application of the resistant sensor to atmospheric pollutants in an urban environment 341
9.5.2.1. Measurement campaign conducted at Lyon in 1988 342
9.5.2.2. Measurement campaign conducted at Saint Etienne in 1998 . . 345
9.5.3. Application of the potentiometric sensor to the control of car exhaust gas 347
9.5.3.1. Strategy implemented to control the emission of nitrogen oxides 347
9.5.3.2. Strategy implemented to control nitrogen oxide traps 349
9.5.3.3. Results relative to the nitrogen oxides traps 350
9.6. Amelioration of the selectivity properties 352
9.6.1. Amelioration of the selective detection properties of SnO_2 sensors using metallic filters 352
9.6.1.1. Development of a sensor using a rhodium filter. 352
9.6.1.2. Development of a sensor using a platinum filter 354
9.6.2. Development of mechanical filters 356
9.6.2.1. Development of a sensor detecting hydrogen 356
9.6.2.2. Development of a protective film for potentiometric sensors . . 356
9.7. Bibliography 359

Chapter 10. Models and Interpretation of Experimental Results 361

10.1. Introduction 361
10.2. Nickel oxide 362
10.2.1. Kinetic model 365
10.2.2. Simulation of a kinetic model using analog electric circuits. 370
10.2.2.1. Simulation of the curves displaying a maximum 370
10.2.2.2. Simulation of the curves displaying a plateau 377
10.2.3. Physical significance of the measured electric conductivity. 380
10.3. Beta-alumina 380
10.3.1. Physico-chemical and physical aspects of a phenomenon taking place at the electrodes. 380
10.3.1.1. Oxygen species present at the surface of the device. 380
10.3.1.2. Origin of the electric potential 384
10.3.2. Expression of the model. 385
10.3.2.1. The electrode potential. 385
10.3.2.2. Expression of the coverage degree. 389

10.3.2.3. Expression of the theoretical potential difference at the poles of the device . . . 394
10.3.3. Simulation of the results obtained with oxygen . . . 395
10.3.3.1. Behavior as a function of temperature and pressure . . . 395
10.3.3.2. Behavior as a function of electrode size . . . 397
10.3.3.3. Evolution of the surface potential . . . 399
10.3.4. Simulation of the phenomenon in the presence of CO . . . 401
10.3.4.1. Description of the mechanisms considered . . . 401
10.3.4.2. Oxidation mechanisms of carbon monoxide . . . 402
10.3.4.3. Results of the simulation . . . 405
10.4. Tin dioxide . . . 409
10.4.1. Introduction . . . 409
10.4.2. Proposition for a physico-chemical model . . . 410
10.4.3. Phenomenon at the electrodes and role of the thickness of the sensitive film . . . 415
10.4.3.1. Calculation of the conductance G as a function of the thickness of the film . . . 416
10.4.3.2. Mathematical simulation . . . 423
10.5. Bibliography . . . 428

Index . . . 431